EASTERN UNIVERSITY, SRI LANKA SECOND EXAMINATION IN SCIENCE - 2008/2009 FIRST SEMESTER (PROPER/REPEAT) (February 2010) PH 202 ELECTRONICS 1

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Time: 01 hour.

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Answer ALL Questions

- (a) By explaining the meaning of an intrinsic semiconductor, discuss how an intrinsic semiconductor (for example pure germanium) may be converted into:
 - (i) An N-type semiconductor
 - (ii) A P-type semiconductor

Discuss the mechanism of electrical conduction in the above two cases.

(b) At room temperature, for the germanium intrinsic semiconductor, the mobility of electrons approximately doubled the mobility of holes. The mobility of electrons in the semiconductor is $0.36 \text{ m}^2 \text{ V}^{-1} \text{s}^{-1}$. If the electrons and holes densities are equal and is $2.5 \times 10^{19} \text{ m}^{-3}$, find the conductivity of the semiconductor.

2. Briefly explain the action of a bipolar junction transistor.

Sketch and explain the input and output characteristics curves of a transistor.

A silicon transistor is used in the biasing arrangement as shown in the figure below $R_2=5k\Omega$, $R_C=5k\Omega$, $R_E=10k\Omega$ and $V_{CC}=15V$.

a.



If the base voltage is 5V find:

- (i) The value of R_1
- (ii) The emitter voltage
- (iii)The emitter current
- (iv)The collector current
- (v) The voltage across R_c
- (vi) The collector voltage